Features

- **Fast Read Access Time - 100 ns**
- **Unregulated Battery Power Supply Range, 2.7 V to 3.6 V**
- **Compatible with JEDEC Standard AT27C040**
- **Low Power CMOS Operation**
  - **20 µA max. Standby**
  - **29 mW max. Active at 5 MHz for V_{CC} = 3.6 V**
- **Wide Selection of JEDEC Standard Packages**
  - **32-Lead 600-mil PDIP and Cerdip**
  - **32-Pad PLCC and LCC**
  - **32-Lead TSOP**
- **High Reliability CMOS Technology**
  - **2,000 V ESD Protection**
  - **200 mA Latchup Immunity**
- **Rapid Programming - 100 µs/byte (typical)**
- **Two-Line Control**
- **CMOS and TTL Compatible Inputs and Outputs**
  - **JEDEC Standard for LVTTL and LVBO**
- **Integrated Product Identification Code**
- **Commercial and Industrial Temperature Ranges**

Description

The AT27BV040 chip is a high performance, low power, low voltage, 4,194,304 bit ultraviolet erasable and electrically programmable read only memory (EPROM) organized as 512K by 8 bits. It requires only one supply in the range of 2.7 to 3.6 V in normal read mode operation, making it ideal for fast, portable systems using either regulated or unregulated battery power.

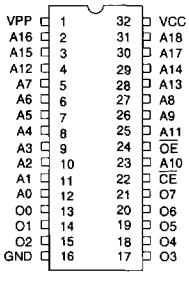
Atmel's innovative design techniques provide fast speeds that rival 5-V parts while keeping the low power consumption of a 3-V supply. At V_{CC} = 2.7 V, any byte can be accessed in less than 100 ns. With a typical power draw of only 18 mW at 5 MHz and V_{CC} = 3 V, the AT27BV040 consumes less than one-fifth the power of a standard 5-V EPROM. Standby mode supply current is typically less than 1 µA at 3 V. The AT27BV040 simplifies system design and stretches battery lifetime even further by eliminating the need for power supply regulation.

(continued)

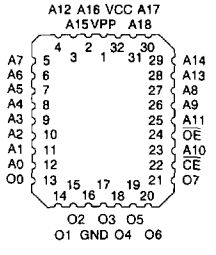
Pin Configurations

Pin Name	Function
A0-A18	Addresses
O0-O7	Outputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable

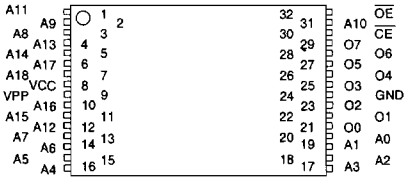
CDIP, PDIP Top View



LCC, PLCC Top View



TSOP Top View
Type 1



3

4 Megabit (512K x 8) Unregulated *Battery-Voltage* High Speed UV Erasable CMOS EPROM

Preliminary

Description (Continued)

The AT27BV040 comes in a choice of industry standard JEDEC-approved packages, including: one-time programmable (OTP) plastic PDIP, PLCC, and TSOP, as well as windowed ceramic Cerdip and LCC. All devices feature two-line control ($\overline{CE}$, $\overline{OE}$) to give designers the flexibility to prevent bus contention.

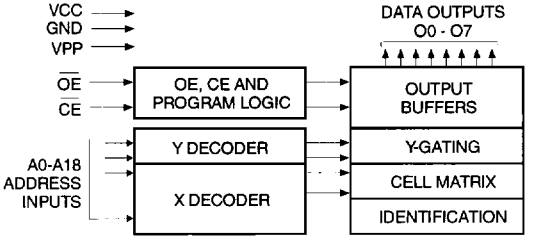
The AT27BV040 operating with V_{CC} at 3.0 V produces TTL level outputs that are compatible with standard TTL logic devices operating at V_{CC} = 5.0 V. At V_{CC} = 2.7 V, the part is compatible with JEDEC approved low voltage battery operation (LVBO) interface specifications.

Atmel's AT27BV040 has additional features to ensure high quality and efficient production use. The Rapid Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 µs/byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27BV040 programs exactly the same way as a standard 5-V AT27C040 and uses the same programming equipment.

Erasure Characteristics

The entire memory array of the AT27BV040 is erased (all outputs read as V_{OH}) after exposure to ultraviolet light at a wavelength of 2537 Å. Complete erasure is assured after a minimum of 20 minutes exposure using 12,000 µW/cm^2 intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of 15 W•sec/cm^2. To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias	-40°C to +85°C
Storage Temperature	-65°C to +125°C
Voltage on Any Pin with Respect to Ground	-2.0 V to +7.0 V(1)
Voltage on A9 with Respect to Ground	-2.0 V to +14.0 V(1)
V_{PP} Supply Voltage with Respect to Ground	-2.0 V to +14.0 V(1)
Integrated UV Erase Dose	7258 W•sec/cm^2

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note:
1. Minimum voltage is -0.6 V dc which may undershoot to -2.0 V for pulses of less than 20 ns. Maximum output pin voltage is V_{CC} + 0.75 V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0 V for pulses of less than 20 ns.

Operating Modes

Mode \ Pin	$\overline{CE}$	$\overline{OE}$	Ai	V_{PP}	V_{CC}	Outputs
Read(2)	V_{IL}	V_{IL}	Ai	X(1)	V_{CC} (2)	D_{OUT}
Output Disable(2)	X	V_{IH}	X	X	V_{CC} (2)	High Z
Standby(2)	V_{IH}	X	X	X	V_{CC} (2)	High Z
Rapid Program(3)	V_{IL}	V_{IH}	Ai	V_{PP}	V_{CC} (3)	D_{IN}
PGM Verify(3)	X	V_{IL}	Ai	V_{PP}	V_{CC} (3)	D_{OUT}
PGM Inhibit(3)	V_{IH}	V_{IH}	X	V_{PP}	V_{CC} (3)	High Z
Product Identification(3),(5)	V_{IL}	V_{IL}	A9=V_H (4) A0=V_{IH} or V_{IL} A1-A18=V_{IL}	X	V_{CC} (3)	Identification Code

Notes: 1. X can be V_{IL} or V_{IH}.
2. Read, output disable, and standby modes require $V_{CC} \leq 3.7$ V.
3. Refer to Programming Characteristics. Programming modes require $V_{CC} \geq 4.5$ V.
4. $V_H = 12.0 \pm 0.5$ V.
5. Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9 which is set to V_H and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

D.C. and A.C. Operating Conditions for Read Operation

		AT27BV040		
		-10	-12	-15
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
V_{CC} Power Supply		2.7 V to 3.6 V	2.7 V to 3.6 V	2.7 V to 3.6 V

3

D.C. and Operating Characteristics for Read Operation

(V_{CC} = 2.7 V to 3.6 V unless otherwise specified)

Symbol	Parameter	Condition		Min	Max	Units
I_{LI}	Input Load Current	V_{IN} = 0 V to V_{CC}			±1	µA
I_{LO}	Output Leakage Current	V_{OUT} = 0 V to V_{CC}			±5	µA
I_{PP1} [2]	V_{PP} [1] Read/Standby Current	V_{PP} = V_{CC}			10	µA
I_{SB}	V_{CC} [1] Standby Current	I_{SB1} (CMOS), $\overline{CE}$ = V_{CC} ± 0.3 V			20	µA
		I_{SB2} (TTL), $\overline{CE}$ = 2.0 to V_{CC} + 0.5 V			100	µA
I_{CC}	V_{CC} Active Current	f = 5 MHz, I_{OUT} = 0 mA, $\overline{CE}$ = V_{IL}, V_{CC} = 3.6 V	Com.		8	mA
			Ind.		10	mA
V_{IL}	Input Low Voltage	V_{CC} = 3.0 to 3.6 V		-0.6	0.8	V
		V_{CC} = 2.7 to 3.6 V		-0.6	0.2xV_{CC}	V
V_{IH}	Input High Voltage	V_{CC} = 3.0 to 3.6 V		2.0	V_{CC}+0.5	V
		V_{CC} = 2.7 to 3.6 V		0.7xV_{CC}	V_{CC}+0.5	V
V_{OL}	Output Low Voltage	I_{OL} = 2.0 mA			0.4	V
		I_{OL} = 100 µA			0.2	V
		I_{OL} = 20 µA			0.1	V
V_{OH}	Output High Voltage	I_{OH} = -2.0 mA		2.4		V
		I_{OH} = -100 µA		V_{CC}-0.2		V
		I_{OH} = -20 µA		V_{CC}-0.1		V

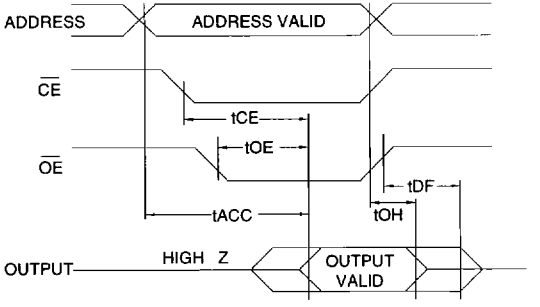
Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP}, and removed simultaneously with or after V_{PP}. 2. V_{PP} may be connected directly to V_{CC}, except during programming. The supply current would then be the sum of I_{CC} and I_{PP}.

A.C. Characteristics for Read Operation (V_{CC} = 2.7 V to 3.6 V)

			AT27BV040						
			-10		-12		-15		
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Units
t_{ACC} [3]	Address to Output Delay	$\overline{CE}$ = $\overline{OE}$ = V_{IL}		100		120		150	ns
t_{CE} [2]	$\overline{CE}$ to Output Delay	$\overline{OE}$ = V_{IL}		100		120		150	ns
t_{OE} [2,3]	$\overline{OE}$ to Output Delay	$\overline{CE}$ = V_{IL}		50		50		60	ns
t_{DF} [4,5]	$\overline{OE}$ or $\overline{CE}$ High to Output Float			40		40		50	ns
t_{OH}	Output Hold from Address, $\overline{CE}$ or $\overline{OE}$, whichever occurred first		0		0		0		ns

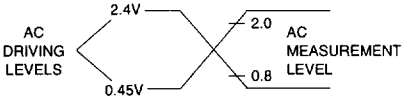
Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.

A.C. Waveforms for Read Operation [1]



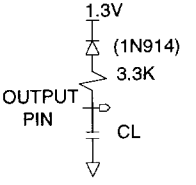
Notes:
1. Timing measurement references are 0.8 V and 2.0 V. Input AC driving levels are 0.45 V and 2.4 V. See Input Test Waveforms and Measurement Levels.
2. $\overline{OE}$ may be delayed up to t_{CE}-t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}.
3. $\overline{OE}$ may be delayed up to t_{ACC}-t_{OE} after the address is valid without impact on t_{ACC}.
4. This parameter is only sampled and is not 100% tested.
5. Output float is defined as the point when data is no longer driven.

Input Test Waveform and Measurement Level



t_R, t_F < 20 ns (10% to 90%)

Output Test Load



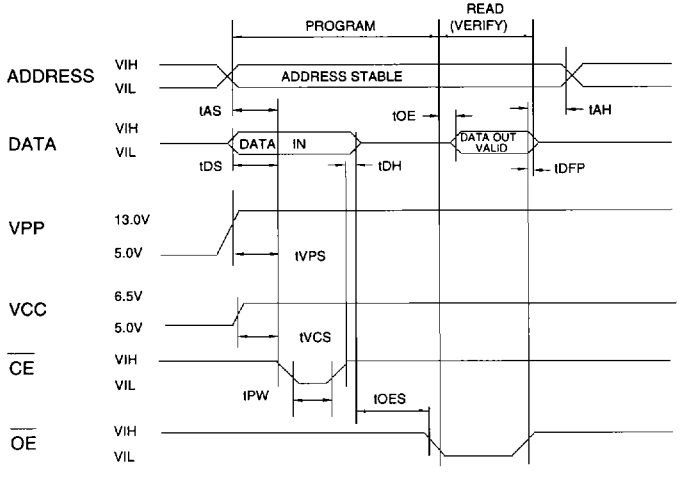
Note: C_L = 100 pF including jig capacitance.

Pin Capacitance (f = 1 MHz, T = 25°C) [1]

	Typ	Max	Units	Conditions
C_{IN}	4	8	pF	V_{IN} = 0 V
C_{OUT}	8	12	pF	V_{OUT} = 0 V

Notes: 1. Typical values for nominal supply voltage. This parameter is only sampled and is not 100% tested.

Programming Waveforms [1]



Notes:
1. The Input Timing Reference is 0.8 V for V_{IL} and 2.0 V for V_{IH}.
2. t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.
3. When programming the AT27BV040 a 0.1-µF capacitor is required across V_{PP} and ground to suppress spurious voltage transients.

D.C. Programming Characteristics

$T_A = 25 \pm 5°C$, $V_{CC} = 6.5 \pm 0.25$ V, $V_{PP} = 13.0 \pm 0.25$ V

Symbol	Parameter	Test Conditions	Limits Min	Limits Max	Units
I_{LI}	Input Load Current	$V_{IN}=V_{IL},V_{IH}$		10	µA
V_{IL}	Input Low Level	(All Inputs)	-0.6	0.8	V
V_{IH}	Input High Level		2.0	$V_{CC}+.7$	V
V_{OL}	Output Low Volt.	$I_{OL}=2.1$ mA		.45	V
V_{OH}	Output High Volt.	$I_{OH}=-400$ µA	2.4		V
I_{CC2}	V_{CC} Supply Current (Program and Verify)			40	mA
I_{PP2}	V_{PP} Supply Current	$\overline{CE}=V_{IL}$		20	mA
V_{ID}	A9 Product Identification Voltage		11.5	12.5	V

A.C. Programming Characteristics

$T_A = 25 \pm 5°C$, $V_{CC} = 6.5 \pm 0.25$ V, $V_{PP} = 13.0 \pm 0.25$ V

Symbol	Parameter	Test Conditions* (see Note 1)	Limits Min	Limits Max	Units
t_{AS}	Address Setup Time		2		µs
t_{OES}	$\overline{OE}$ Setup Time		2		µs
t_{DS}	Data Setup Time		2		µs
t_{AH}	Address Hold Time		0		µs
t_{DH}	Data Hold Time		2		µs
t_{DFP}	$\overline{OE}$ High to Output Float Delay	(Note 2)	0	130	ns
t_{VPS}	V_{PP} Setup Time		2		µs
t_{VCS}	V_{CC} Setup Time		2		µs
t_{PW}	$\overline{CE}$ Program Pulse Width	(Note 3)	95	105	µs
t_{OE}	Data Valid from $\overline{OE}$	(Note 2)		150	ns

*A.C. Conditions of Test:

Input Rise and Fall Times (10% to 90%) ..... 20 ns
Input Pulse Levels ..... 0.45 V to 2.4 V
Input Timing Reference Level ..... 0.8 V to 2.0 V
Output Timing Reference Level ..... 0.8 V to 2.0 V

Notes:

1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
2. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven — see timing diagram.
3. Program Pulse width tolerance is 100 µsec ± 5%.

Atmel's 27BV040 Integrated Product Identification Code[1]

Codes	A0	O7	O6	O5	O4	O3	O2	O1	O0	Hex Data
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	0	0	0	0	1	0	1	1	0B

Note: 1. The AT27BV040 has the same Product Identification Code as the AT27C040. Both are programming compatible.

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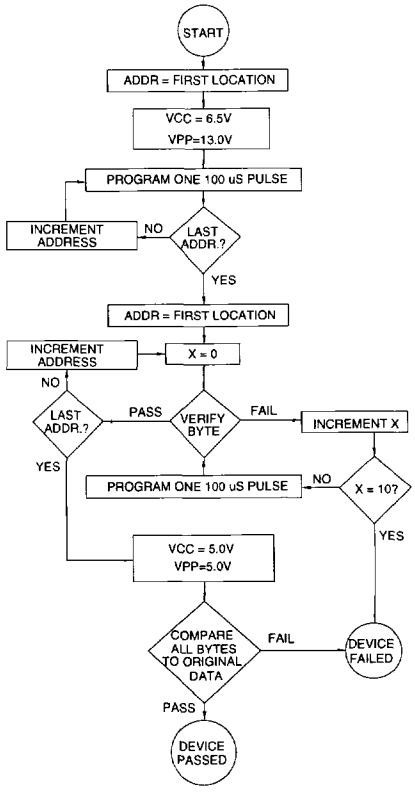
Rapid Programming Algorithm

A 100 µs $\overline{CE}$ pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5 V and V_{PP} is raised to 13.0 V. Each address is first programmed with one 100 µs $\overline{CE}$ pulse without verification. Then a verification/reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 µs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. V_{PP} is then lowered to 5.0 V and V_{CC} to 5.0 V. All bytes are read again and compared with the original data to determine if the device passes or fails.



Ordering Information

t_{ACC} (ns)	I_{CC} (mA) V_{CC} = 3.6 V		Ordering Code	Package	Operation Range
	Active	Standby			
100	8	0.02	AT27BV040-10DC AT27BV040-10JC AT27BV040-10LC AT27BV040-10PC AT27BV040-10TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)
100	10	0.02	AT27BV040-10DI AT27BV040-10JI AT27BV040-10LI AT27BV040-10PI AT27BV040-10TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)
120	8	0.02	AT27BV040-12DC AT27BV040-12JC AT27BV040-12LC AT27BV040-12PC AT27BV040-12TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)
120	10	0.02	AT27BV040-12DI AT27BV040-12JI AT27BV040-12LI AT27BV040-12PI AT27BV040-12TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)
150	8	0.02	AT27BV040-15DC AT27BV040-15JC AT27BV040-15LC AT27BV040-15PC AT27BV040-15TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)
150	10	0.02	AT27BV040-15DI AT27BV040-15JI AT27BV040-15LI AT27BV040-15PI AT27BV040-15TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)

Package Type	
32DW6	32 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)
32P6	32 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)
32T	32 Lead, Plastic Thin Small Outline Package OTP (TSOP)